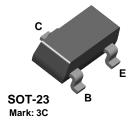


MPS5179

MMBT5179

PN5179







NPN RF Transistor

This device is designed for use in low noise UHF/VHF amplifiers with collector currents in the 100 µA to 30 mA range in common emitter or common base mode of operation, and in low frequency drift, high ouput UHF oscillators. Sourced from Process 40.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	12	V
V _{CBO}	Collector-Base Voltage	20	V
V _{EBO}	Emitter-Base Voltage	2.5	V
Ic	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

 $\label{eq:NOTES:1} \mbox{NOTES:}$ 1) These ratings are based on a maximum junction temperature of 150 degrees C.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	M	Units	
		PN/MPS5179	*MMBT5179	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

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NPN RF Transistor

(continued)

Electrica	l Charact	erist	ics
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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OEE CHAI	RACTERISTICS				
		_		1	1
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	12		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 1.0 \mu A, I_E = 0$	20		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	2.5		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$		0.02	μΑ
		$V_{CB} = 15 \text{ V}, T_A = 150 ^{\circ}\text{C}$		1.0	μA

ON CHARACTERISTICS

h _{FE}	DC Current Gain	$I_C = 3.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	25	250	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		1.0	V

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_C = 5.0 \text{ mA}, V_{CE} = 6.0 \text{ V},$ f = 100 MHz	900	2000	MHz
C _{cb}	Collector-Base Capacitance	V _{CB} = 10 V, I _E = 0, f = 0.1 to 1.0 MHz		1.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 6.0 \text{ V},$ f = 1.0 kHz	25	300	
rb'C _c	Collector Base Time Constant	$I_C = 2.0 \text{ mA}, V_{CB} = 6.0 \text{ V},$ f = 31.9 MHz	3.0	14	ps
NF	Noise Figure	$I_C = 1.5 \text{ mA}, V_{CE} = 6.0 \text{ V},$ $R_S = 50\Omega, f = 200 \text{ MHz}$		5.0	dB

FUNCTIONAL TEST

G _{pe}	Amplifier Power Gain	$V_{CE} = 6.0 \text{ V}, I_{C} = 5.0 \text{ mA},$ f = 200 MHz	15	dB
Po	Power Output	$V_{CB} = 10 \text{ V}, I_{E} = 12 \text{ mA},$ f $\geq 500 \text{ MHz}$	20	mW

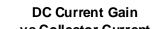
^{*}Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

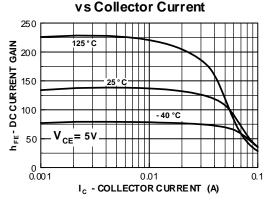
Spice Model

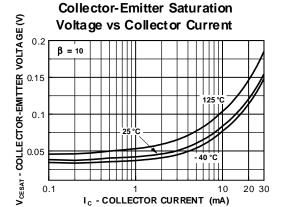
NPN RF Transistor

(continued)

Typical Characteristics



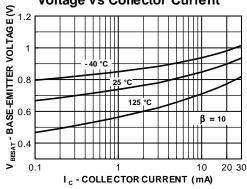


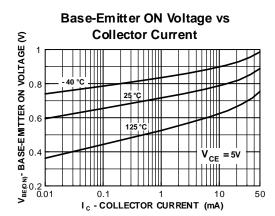


Ic - COLLECTOR CURRENT (mA)

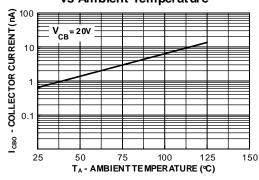
0.1

Base-Emitter Saturation Voltage vs Collector Current

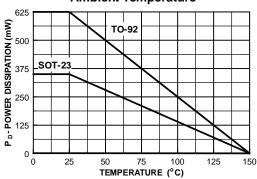




Collector-Cutoff Current vs Ambient Temperature



Power Dissipation vs Ambient Temperature



NPN RF Transistor

(continued)

Test Circuit

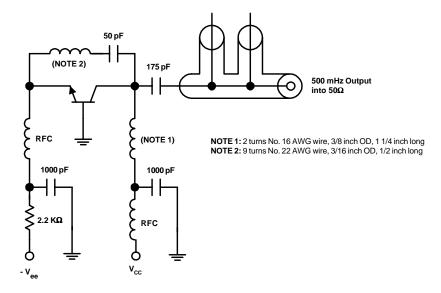
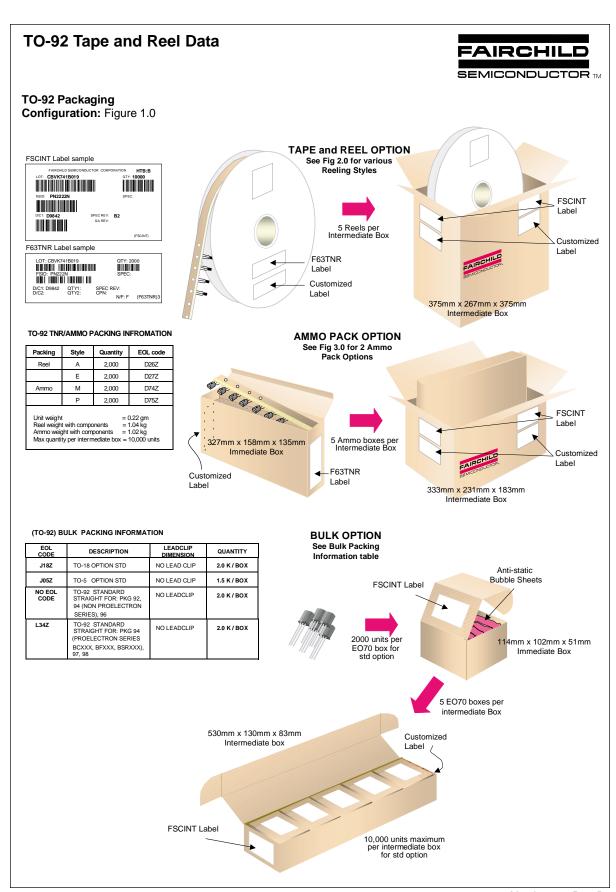


FIGURE 1: 500 MHz Oscillator Circuit

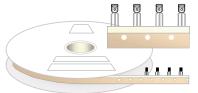


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



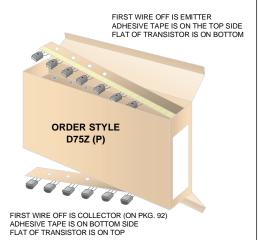
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

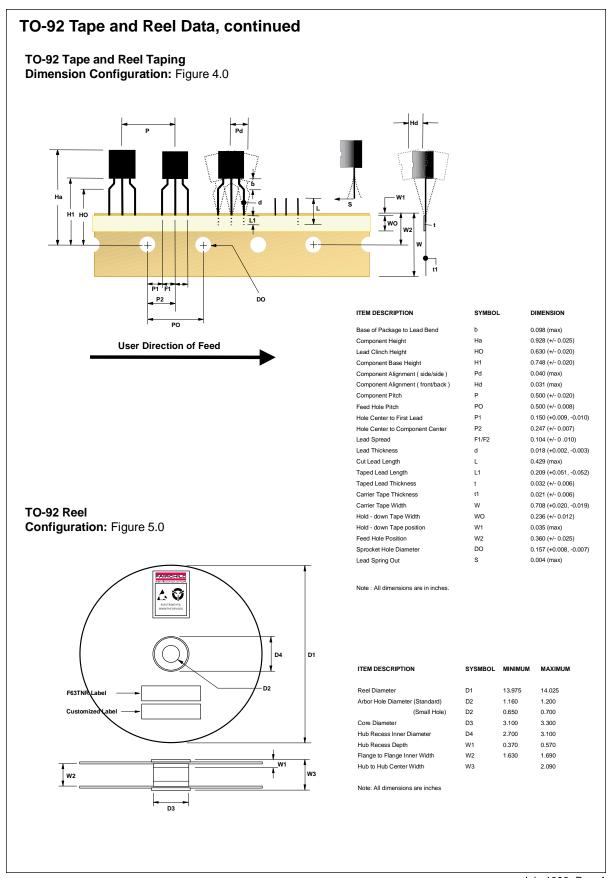
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





September 1999, Rev. B

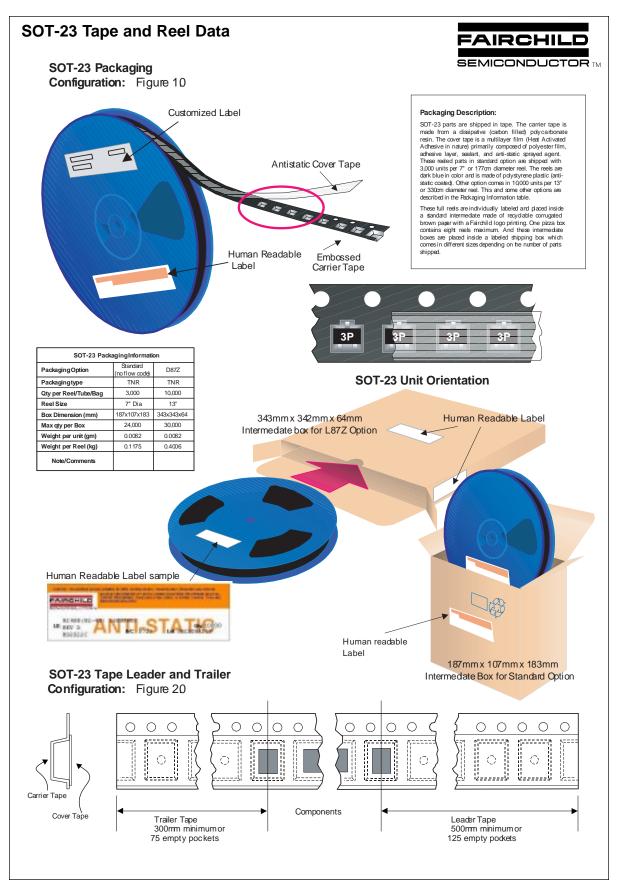


TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

January 2000, Rev. B

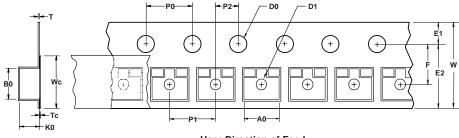


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SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



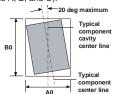
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



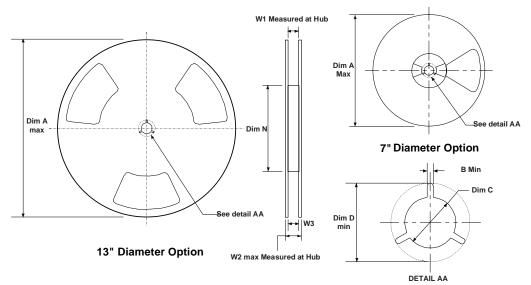
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

SOT-23 Reel Configuration: Figure 4.0

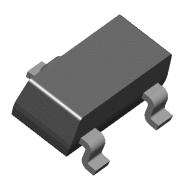


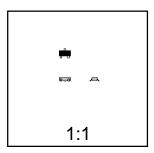
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SOT-23 Package Dimensions



SOT-23 (FS PKG Code 49)

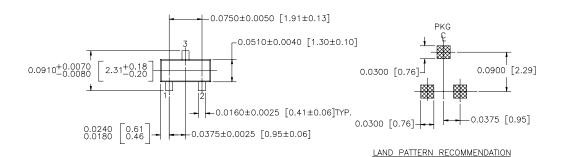


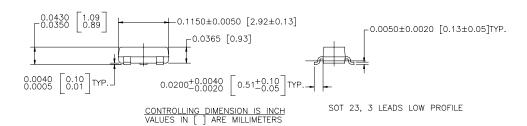


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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